L Number	Hits	Search Text	DB	Time stamp
31	40	lateral near4 zener adj diode	USPAT;	2002/03/07 10:23
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
32	51	(lateral or horizontal) near4 zener adj	USPAT;	2002/03/07 10:23
		diode	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	446	("257/339").CCLS.	USPAT;	2002/03/06 15:19
		(20.,000 , 00000	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
:	1004	("257/355").CCLS.	IBM TDB USPAT;	2002/03/02 21:29
-	1004	(257/355).CCLS.	US-PGPUB;	2002/03/02 21.29
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1672		USPAT;	2002/03/02 21:29
		or (("257/355").CCLS.)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1474		USPAT;	2002/03/02 21:31
		(("257/339").CCLS.) or (("257/355").CCLS.)) and (@pd<20000606 or	US-PGPUB; EPO; JPO;	
		((257/355).CCLS.)) and (epa<2000000 of	DERWENT;	
			IBM TDB	
-	21143	npn same pnp	USPAT;	2002/03/02 21:31
			US-PGPUB;	
'			EPO; JPO; DERWENT;	
			IBM TDB	
_	114		USPAT;	2002/03/02 21:31
		(("257/339").CCLS.) or	US-PGPUB;	
		(("257/355").CCLS.)) and (@pd<20000606 or @rlad<20010609)) and (npn same pnp)	EPO; JPO; DERWENT;	
		ellad 20010003// and (hph same php)	IBM TDB	
_	322	protection adj circuit.ti,ab. and vss	USPAT;	2002/03/03 12:40
			US-PGPUB;	
	ļ		EPO; JPO;	
			DERWENT; IBM TDB	
_	2	protection adj circuit.ti,ab. and vss adj	USPAT;	2002/03/03 12:41
		power adj line and p+ and n+	US-PGPUB;	
			EPO; JPO;	
		·	DERWENT; IBM TDB	
_	314	("257/173").CCLS.	USPAT;	2002/03/03 12:45
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	314	("257/173").CCLS.	IBM TDB USPAT;	2002/03/03 12:46
	314	(25.,2.5 ,.0025.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1_	197	("257/173").CCLS.	IBM TDB USPAT	2002/03/03 13:33
_	23		USPAT;	2002/03/03 13:01
		,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	282	("257/339").CCLS.	IBM TDB USPAT	2002/03/03 13:34
L	202	1 (20,700) 7.000.	1 001111	2002/00/00 10:04

				0000/00/00
-	280	(("257/339").CCLS.) not	USPAT;	2002/03/03 13:46
		(("257/173").CCLS.)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	280	(("257/339").CCLS.) not	USPAT	2002/03/03 14:01
		(("257/173").CCLS.)		
_	501	(257/355.ccls. not 257/173.ccls.) not	USPAT	2002/03/03 15:22
		257/339.ccls.		
_	37	(vertical near2 (npn or pnp) near2	USPAT;	2002/03/03 17:16
		transistor) same protect\$3 same (surge or	US-PGPUB;	
		esd or electrostatic adj discharge or	EPO; JPO;	
		human adj body adj model or hbm or	DERWENT;	
		breakdown adj voltage)	IBM TDB	
_	76		USPAT;	2002/03/03 17:16
		protection	US-PGPUB;	
		,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
l _	15	zener adj diode and mosfet and esd adj	USPAT;	2002/03/03 17:17
	1.5	protection and vss	US-PGPUB;	2002/03/03 17.17
		procection and vss	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	4	adi diada and (mas an masfat) ti ab	1	2002/02/02 18.02
-	4	zener adj diode and (mos or mosfet).ti,ab.	USPAT;	2002/03/03 18:02
		and esd adj protection and vss	US-PGPUB;	•
			EPO; JPO;	
			DERWENT;	
	_		IBM TDB	
-	4	zener adj diode and (mos or mosfet or	USPAT;	2002/03/03 19:37
		nmosfet or nmos or pmos or pmosfet or	US-PGPUB;	
		field adj effect adj transistor).ti,ab.	EPO; JPO;	
		and (electrostatic adj discharge or esd)	DERWENT;	
		adj protection.ti,ab. and vss	IBM TDB	
-	2		USPAT	2002/03/03 19:38
-	0	("prevent adj latch-up.ti,ab.").PN.	USPAT;	2002/03/03 20:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	462	prevent adj latch-up.ti,ab.	USPAT;	2002/03/03 20:19
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	44	prevent adj latch-up.ti,ab.	USPAT	2002/03/03 20:19
i -	13	integrated adj circuit.ti,ab. and (prevent	USPAT	2002/03/03 20:19
		adj latch-up).ti,ab.		
-	0	09/866,782.ap.	USPAT;	2002/03/05 20:29
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	"08-101176"	JPO	2002/03/05 20:36
-	17	dairitsu	JPO	2002/03/05 20:36
-	25	dairitsu	JPO;	2002/03/05 20:37
			DERWENT	
-	317	("257/173").CCLS.	USPAT;	2002/03/05 21:38
]	· · · · · · · · · · · · · · · · · · ·	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
_	446	("257/339").CCLS.	USPAT;	2002/03/05 21:38
	440	\ 23//335 /.CCES.	US-PGPUB;	2002,00,00 21.00
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
l			ממז נוסד	1

	1005	(#057/255#) 0010	HODAW.	2002/03/05 21:38
-	1005	("257/355").CCLS.	USPAT; US-PGPUB;	2002/03/05 21:38
			EPO; JPO;	
			DERWENT;	
	1.575	(/#057/172#)	IBM TDB	2002/03/05 21:40
-	1675	(("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)	USPAT; US-PGPUB;	2002/03/05 21:40
		01 ((237/333):0013.)	EPO; JPO;	
			DERWENT;	
	_		IBM TDB	0000 (00 (05 01 01
-	2	((("257/173").CCLS.) or (("257/339").CCLS.) or	USPAT; US-PGPUB;	2002/03/05 21:44
		(("257/355").CCLS.)) and silicide and (esd	EPO; JPO;	
		or electrostatic adj discharge or hbm or	DERWENT;	
,		human adj body adj model or surge).ti,ab.	IBM TDB	
		and (mos or nmos or pmos or dmos or ldmos or mosfet or nmosfet or pmosfet or dmosfet		
		or ldmosfet).ti,ab. and zener and bipolar		
- X		adj transistor		
-	3		USPAT;	2002/03/05 21:56
		(("257/339").CCLS.) or	US-PGPUB;	
		(("257/355").CCLS.)) and silicide and (esd or electrostatic adj discharge or hbm or	EPO; JPO; DERWENT;	
		human adj body adj model or surge or	IBM TDB	
		protection).ti,ab. and (mos or nmos or		
		pmos or dmos or ldmos or mosfet or nmosfet		
		or pmosfet or dmosfet or ldmosfet).ti,ab. and zener and bipolar adj transistor		
-	6	((("257/173").CCLS.) or	USPAT;	2002/03/05 22:00
		(("257/339").CCLS.) or	US-PGPUB;	
		(("257/355").CCLS.)) and silicide and (esd	EPO; JPO;	
		or electrostatic adj discharge or hbm or human adj body adj model or surge or	DERWENT; IBM TDB	
		protection).ti,ab. and (mos or nmos or		
		pmos or dmos or ldmos or mosfet or nmosfet		
		or pmosfet or dmosfet or ldmosfet).ti,ab.		
_	36	and zener ((("257/173").CCLS.) or	USPAT;	2002/03/05 22:00
	30	(("257/339").CCLS.) or	US-PGPUB;	2002,00,00 22.00
		(("257/355").CCLS.)) and (esd or	EPO; JPO;	
		electrostatic adj discharge or hbm or	DERWENT;	
	İ	human adj body adj model or surge or protection).ti,ab. and (mos or nmos or	IBM TDB	
		pmos or dmos or ldmos or mosfet or nmosfet		
		or pmosfet or dmosfet or ldmosfet).ti,ab.		
		and zener	HODE TO	2002/02/26 22 11
_	0	(MOS or MOSFET) near12 protect\$3 near12 (each adj other)	USPAT; US-PGPUB;	2002/03/06 08:44
		(caon ad) other)	EPO; JPO;	
			DERWENT;	
			IBM TDB	2002/03/06 08:55
-	28	plurality adj2 (mos or mosfet) and (esd or electrostatic adj discharge) adj protect\$3	USPAT; US-PGPUB;	2002/03/06 08:55
		described and arboharge, and proceedings	EPO; JPO;	
			DERWENT;	
	_		IBM TDB	2002/02/06 00-56
_	0	mosfet adj array and esd adj protection.ti,ab.	USPAT; US-PGPUB;	2002/03/06 08:56
		, , , , , , , , , , , , , , , , , , , ,	EPO; JPO;	:
			DERWENT;	
			IBM TDB	2002/02/06 14:00
-	4	mosfet adj array and esd adj protection	USPAT; US-PGPUB;	2002/03/06 14:00
			EPO; JPO;	
			DERWENT;	
			IBM TDB	2002/02/06 24 25
_	2466	phosphor\$3 near6 dopant near6 type	USPAT;	2002/03/06 14:16
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	

-	4	Schottky adj diode same silicide adj2	USPAT;	2002/03/06 14:19
		(layer or film) same protect\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	2002/02/06 14:10
_	0	Schottky adj diode same silicide adj2	USPAT;	2002/03/06 14:19
		(layer or film) same esd adj protect\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1.0		IBM TDB	2002/03/06 14:46
-	19	Schottky adj diode same esd adj protect\$3	USPAT;	2002/03/06 14:46
		·	US-PGPUB; EPO; JPO;	
		*	DERWENT;	
			IBM TDB	
_ `	4	silicide adj (layer or film) same current	USPAT;	2002/03/06 14:56
	1	same decreas\$3 same schottky	US-PGPUB;	2002/03/00 14:30
		bane dedicaby band bonoceny	EPO; JPO;	
		· ·	DERWENT;	
			IBM TDB	
_	54	schottky adj diode same protection adj2	USPAT;	2002/03/06 14:58
		circuit	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	schottky adj diode same protection adj2	USPAT;	2002/03/06 14:58
i		circuit same silicide	US-PGPUB;	
	ļ		EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	50	1 '	USPAT;	2002/03/06 15:25
		(layer or film) or salicide)) and (esd or	US-PGPUB;	
		electrostatic adj discharge or protect\$3	EPO; JPO;	
		or hbm or human adj body adj model or	DERWENT;	
	4	surge)	IBM TDB	2002/03/06 15:47
-	4	(schottky adj diode near12 (silicide adj (layer or film) or salicide)) and (esd or	USPAT; US-PGPUB;	2002/03/06 15:47
	_	electrostatic adj discharge or protect\$3	EPO; JPO;	
		or hbm or human adj body adj model or	DERWENT;	
		surge).ti,ab.	IBM TDB	
_	3	5166089.pn.	USPAT;	2002/03/06 15:50
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	jp-406224376\$-\$.did.	USPAT;	2002/03/06 15:50
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	2	in-062242766-6 did	IBM TDB	2002/03/06 16:22
- .	2	jp-06224376\$-\$.did.	USPAT; US-PGPUB;	2002/03/06 16:22
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	62	amerasekera.in.	USPAT;	2002/03/06 16:22
	02	amoradonora, in	US-PGPUB;	2002,00,00 10.22
			EPO; JPO;	
		, in the second	DERWENT;	
			IBM TDB	
-	23	amerasekera.in. and bipolar adj transistor	USPAT;	2002/03/06 17:25
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	((triple adj well or triple-well) same	USPAT;	2002/03/06 16:46
		bipolar adj transistor) and third adj2	US-PGPUB;	
		diffusion	EPO; JPO;	
			DERWENT;	
	<u></u>		IBM TDB	

_	33	(triple adj well or triple-well) same bipolar adj transistor	USPAT; US-PGPUB;	2002/03/06 16:47
	:		EPO; JPO; DERWENT;	
	30	(triple add well or triple-well) game	IBM TDB USPAT;	2002/03/06 16:48
_	30	(triple adj well or triple-well) same bipolar adj transistor and (MOS or NMOS or	US-PGPUB;	2002/03/00 10.48
		PMOS or mosfet or pmosfet or nmosfet or	EPO; JPO;	
		cmos or cmosfet)	DERWENT;	
	_		IBM TDB	
-	5	(triple adj well or triple-well) same	USPAT;	2002/03/06 16:58
		bipolar adj transistor and (MOS or NMOS or PMOS or mosfet or pmosfet or nmosfet or	US-PGPUB; EPO; JPO;	
		cmos or cmosfet).ti,ab.	DERWENT;	
			IBM TDB	
-	6	"5872032"	USPAT;	2002/03/06 16:53
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	3	5872032.pn.	USPAT;	2002/03/06 16:53
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	1	(triple adj well or triple-well) same	USPAT;	2002/03/06 17:00
	Ì	bipolar adj transistor and (MOS or NMOS or	US-PGPUB;	
		PMOS or mosfet or pmosfet or nmosfet or	EPO; JPO;	
		cmos or cmosfet).ti,ab. and protect\$3	DERWENT; IBM TDB	
_	1	(protect\$3 same (triple adj well or	USPAT;	2002/03/06 17:04
		triple-well) same bipolar adj transistor)	US-PGPUB;	
		and (MOS or NMOS or PMOS or mosfet or	EPO; JPO;	
		pmosfet or nmosfet or cmos or cmosfet)	DERWENT; IBM TDB	
_	52	protect\$3 and ((third near2 (impurity or	USPAT;	2002/03/06 17:06
		diffusion)) same bipolar adj transistor)	US-PGPUB;	
		and (MOS or NMOS or PMOS or mosfet or	EPO; JPO;	
		pmosfet or nmosfet or cmos or cmosfet)	DERWENT; IBM TDB	
_	12	protect\$3.ti,ab. and ((third near2	USPAT;	2002/03/06 17:07
	ŧ.	(impurity or diffusion)) same bipolar adj	US-PGPUB;	
		transistor) and (MOS or NMOS or PMOS or	EPO; JPO;	
		mosfet or pmosfet or nmosfet or cmos or cmosfet).ti,ab.	DERWENT; IBM TDB	
_	317	("257/173").CCLS.	USPAT;	2002/03/06 17:48
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	760	(zener adj diode near12 (source or drain))	IBM TDB USPAT;	2002/03/07 07:57
		and (electrostatic adj discharge or surge	US-PGPUB;	
		or esd)	EPO; JPO;	
			DERWENT;	
_	196	 (zener adj diode nearl2 (source or drain))	IBM TDB USPAT;	2002/03/07 07:58
		and (electrostatic adj discharge or surge	US-PGPUB;	
		or esd).ti,ab.	EPO; JPO;	
			DERWENT; IBM TDB	
_	157	(zener adj diode near6 (source or drain))	USPAT;	2002/03/07 08:02
	10,	and (electrostatic adj discharge or surge	US-PGPUB;	, 30, 0, 00.02
1		or esd).ti,ab.	EPO; JPO;	
-			DERWENT;	
_	12	(zener adj diode near6 (source or drain))	IBM TDB USPAT;	2002/03/07 08:09
		and (electrostatic adj discharge or surge	US-PGPUB;	
		or esd) and (mos or mosfet or nmos or	EPO; JPO;	
		nmosfet or pmos or pmosfet or dmos or	DERWENT;	
		dmosfet or ldmos or ldmosfet) and (silicide or salicide)	IBM TDB	
	L	(Difference)	l <u> </u>	I

	1	(1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-	USPAT;	2002/02/07 00 00
-	0	(lateral adj zener adj diode near6 (source	USPAT; US-PGPUB;	2002/03/07 08:09
		or drain)) and silicide	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	(lateral add money add diede pears (source	USPAT;	2002/03/07 08:10
_	0	(lateral adj zener adj diode near6 (source or drain))	US-PGPUB;	2002/03/07 08:10
	•	or drain,,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	12	lateral adj zener adj diode	USPAT;	2002/03/07 10:18
_	13	laceral adj Zener adj drode	US-PGPUB;	2002/03/07 10.10
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	57190357.URPN.	USPAT;	2002/03/07 09:23
		37130337.0RIN.	US-PGPUB;	2002/03/07 03:23
			EPO; JPO;	
			DERWENT;	
	İ		IBM TDB	
_	0	57190357.URPN.	USPAT;	2002/03/07 09:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	57190357.URPN.	USPAT;	2002/03/07 09:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	
-	1	"5023521".PN.	USPAT	2002/03/07 09:24